



PE60P50K P-Channel Enhancement Mode Power MOSFET

PE60P50K Description

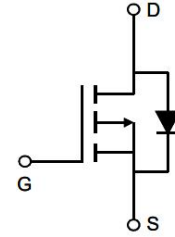
The PE60P50K uses deep trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. It can be used in a wide variety of applications.

PE60P50K General Features

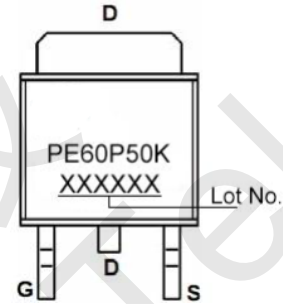
- $V_{DS} = -60V$, $I_D = -50A$
- $R_{DS(ON)} < 25m\Omega @ V_{GS} = -10V$
- $R_{DS(ON)} < 32m\Omega @ V_{GS} = -4.5V$
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

PE60P50K Application

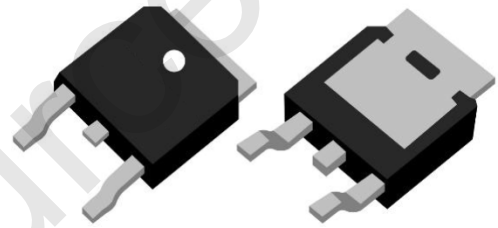
- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



TO-252-2L

PE60P50K Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-50	A
Drain Current-Continuous(TC=100°C)	I_D	-35	A
Pulsed Drain Current (Note 1)	I_{DM}	-150	A
Maximum Power Dissipation	P_D	95	W
Single Pulsed Avalanche Energy(L=0.1mH)	E_{AS}	125	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	°C

PE60P50K Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.6	°C/W
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PE60P50K Electrical Characteristics (TC=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-60V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.2	-1.5	-2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-20A$	-	21	25	m Ω
		$V_{GS}=-4.5V, I_D=-15A$	-	25	32	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-10V, I_D=-20A$	-	45	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=-30V, V_{GS}=0V,$ $F=1.0MHz$	-	1520	-	pF
Output Capacitance	C_{oss}		-	280	-	pF
Reverse Transfer Capacitance	C_{rss}		-	8	-	pF
Gate Resistance	R_g	$V_{GS}=V_{DS}=0V, F=1.0MHz$	-	7	-	Ω
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=-30V, I_D=-20A,$ $V_{GS}=-10V, R_G=3\Omega$	-	7	-	nS
Turn-on Rise Time	t_r		-	5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	65	-	nS
Turn-Off Fall Time	t_f		-	20	-	nS
Total Gate Charge	Q_g	$V_{DS}=-30V, I_D=-20A,$ $V_{GS}=-10V$	-	23	-	nC
Gate-Source Charge	Q_{gs}		-	4	-	nC
Gate-Drain Charge	Q_{gd}		-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-1A$	-	-	-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-50	A
Diode Reverse Recovery Time	t_{rr}	$I_F=-10A, di/dt=100A/\mu s$	-	60	-	nS
Diode Reverse Recovery Charge	Q_{rr}		-	105	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to product.



PE60P50K Typical Electrical and Thermal Characteristics

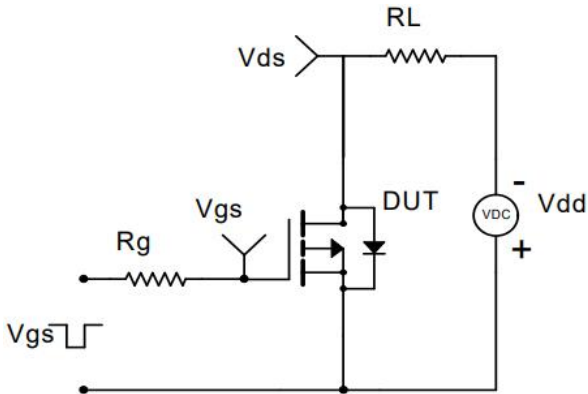


Figure 1 Switching Test Circuit

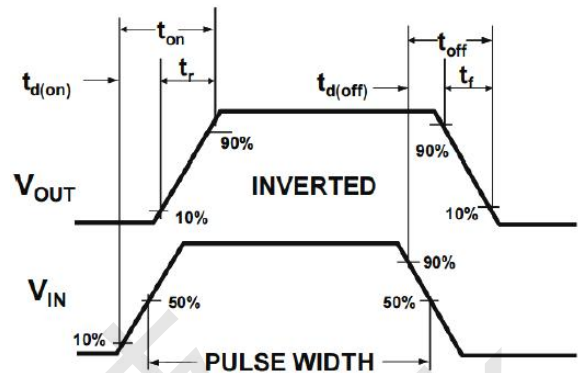


Figure 2 Switching Waveform

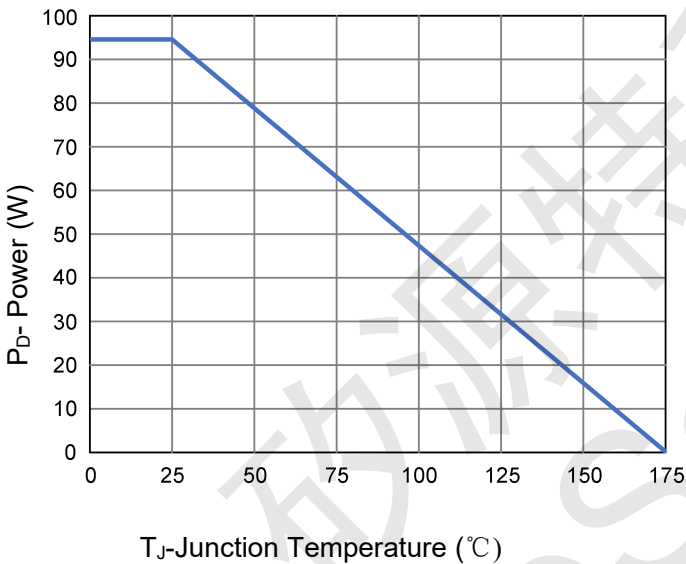


Figure 3 Power De-rating

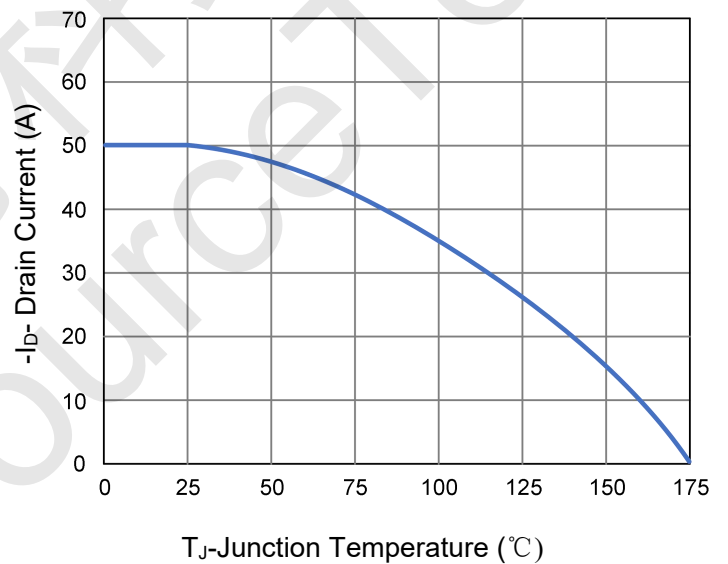


Figure 4 Drain Current

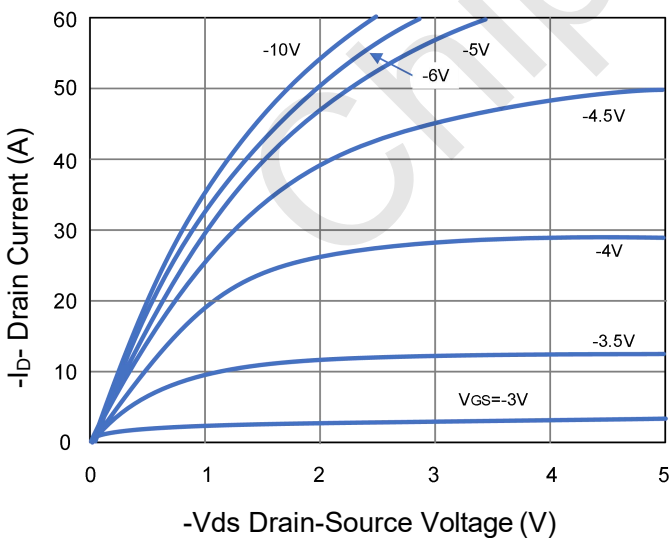


Figure 5 Output Characteristics

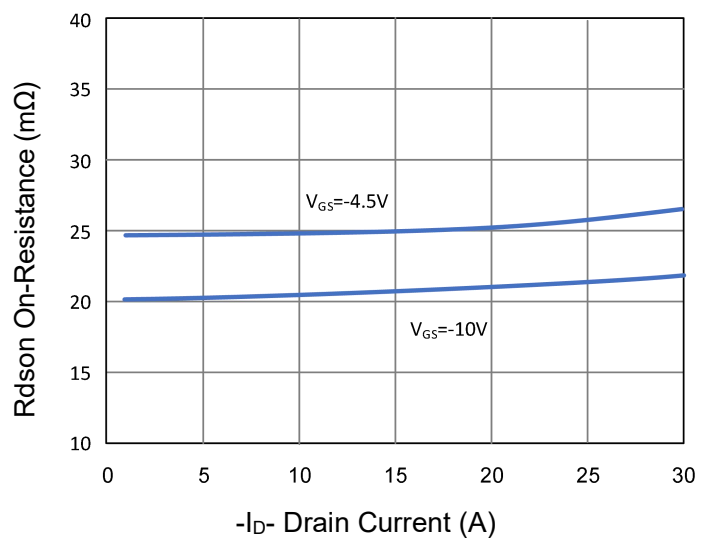


Figure 6 Rdson vs Drain Current

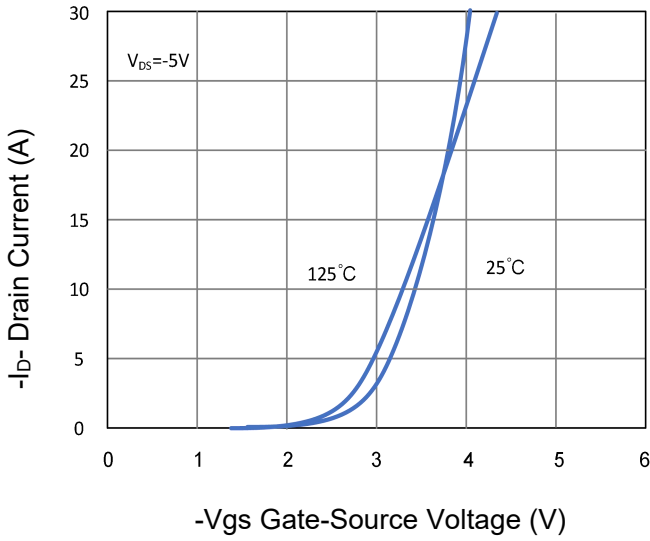


Figure 7 Transfer Characteristics

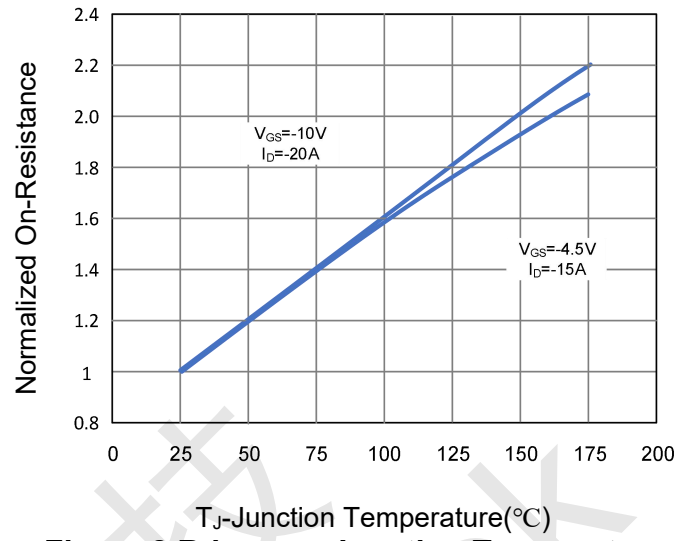


Figure 8 R_{dson} vs Junction Temperature

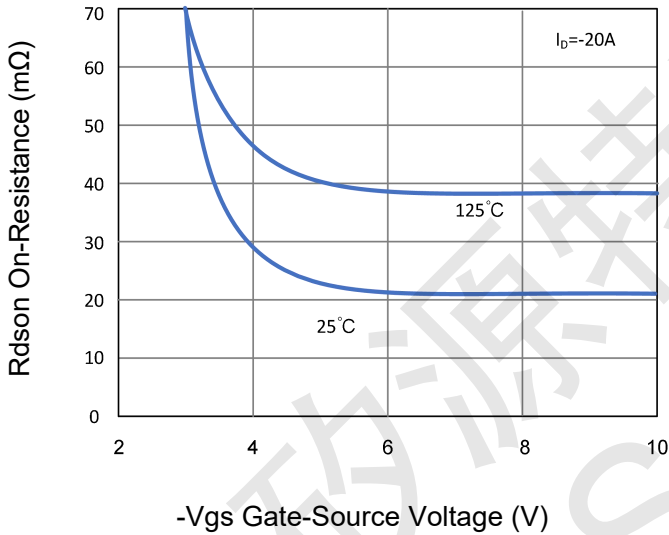


Figure 9 R_{dson} vs V_{GS}

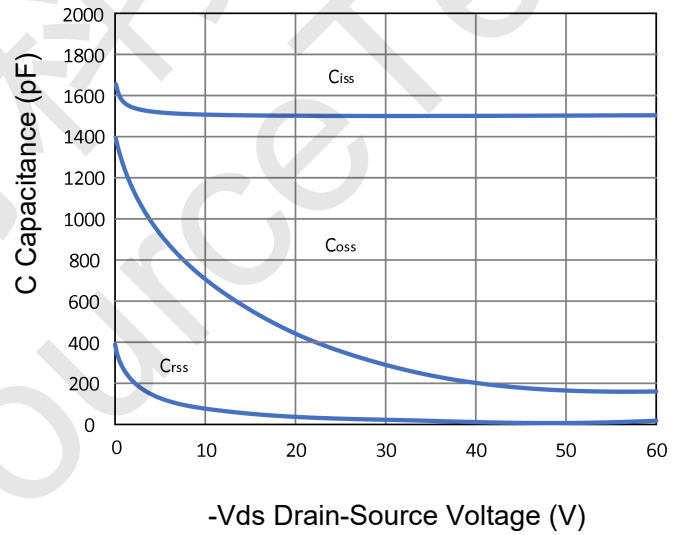


Figure 10 Capacitance vs V_{DS}

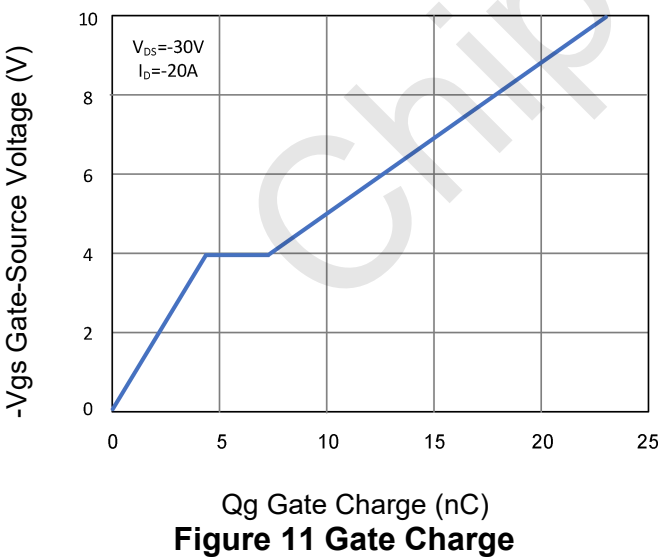


Figure 11 Gate Charge

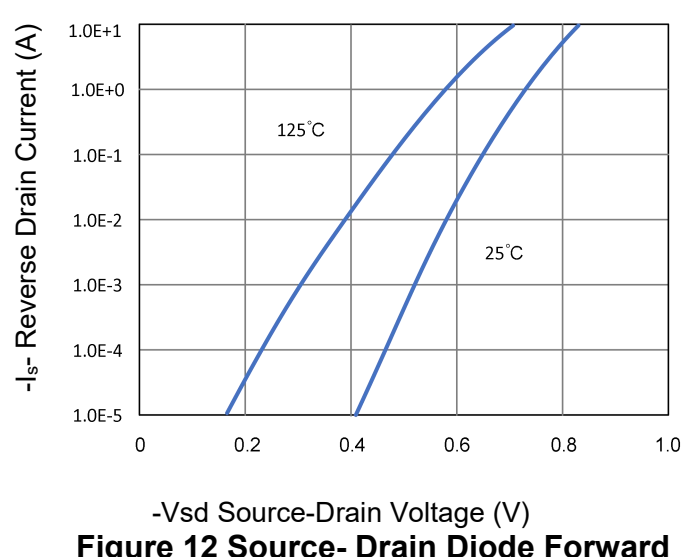


Figure 12 Source- Drain Diode Forward

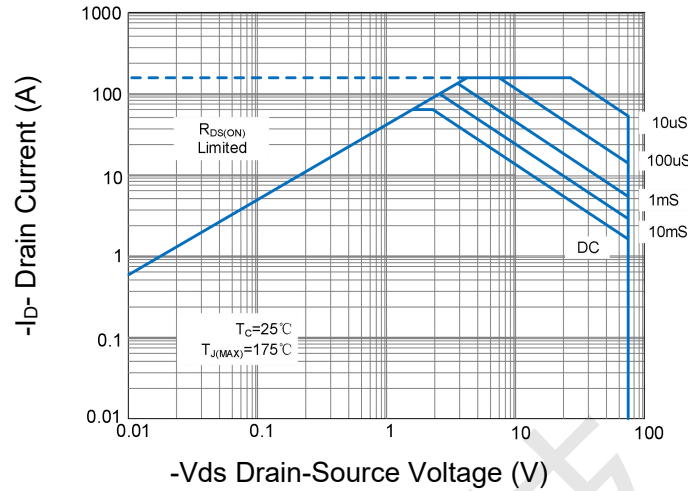


Figure 13 Safe Operation Area

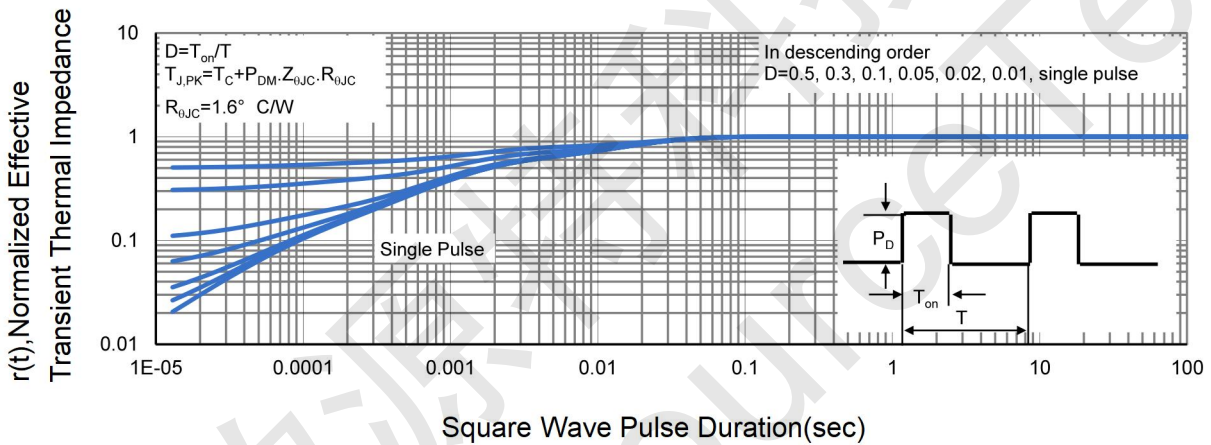


Figure 14 Normalized Maximum Transient Thermal Impedance

